



## **40V N-Channel Enhancement Mode MOSFET**

Voltage

40 V

Current

151 A

#### **Features**

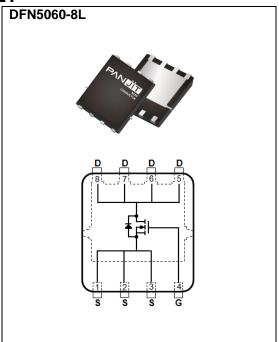
- R<sub>DS(ON)</sub>, V<sub>GS</sub>@10V, I<sub>D</sub>@20A<2.5mΩ
- RDS(ON), VGS@4.5V, ID@20A<3.3m $\Omega$
- Excellent FOM
- Logic Level Drive
- AEC-Q101 qualified
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

#### **Mechanical Data**

• Case: DFN5060-8L Package

• Terminals : Solderable per MIL-STD-750, Method 2026

• Approx. Weight: 0.08 grams



## **Maximum Ratings and Thermal Characteristics** (T<sub>A</sub>=25°C unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS	
Drain-Source Voltage		V <sub>DS</sub>	40	\ \	
Gate-Source Voltage		$V_{GS}$	±20	V	
Continuous Drain Current <sup>(Note 3)</sup>	T <sub>C</sub> =25°C	l <sub>D</sub>	151		
	T <sub>C</sub> =100°C		107	Α	
Pulsed Drain Current(Note 1)	T <sub>C</sub> =25°C	I <sub>DM</sub>	604		
Power Dissipation	T <sub>C</sub> =25°C	P <sub>D</sub>	107	W	
	T <sub>C</sub> =100°C		54		
Continuous Drain Current(Note 4)	T <sub>A</sub> =25°C	l <sub>D</sub>	26.7	^	
	T <sub>A</sub> =70°C		22.3	Α	
Power Dissipation	T <sub>A</sub> =25°C	Po	3.3	W	
	T <sub>A</sub> =70°C	PD	2.3		
Single Pulse Avalanche Energy <sup>(Note 5)</sup>		Eas	240	mJ	
Operating Junction and Storage Temperature Range		T <sub>J</sub> ,T <sub>STG</sub>	-55~175	°C	
Thermal Resistance <sup>(Note 4)</sup>	Junction to Case	R <sub>θJC</sub>	1.4	°C/W	
	Junction to Ambient	$R_{ heta JA}$	45		





### Electrical Characteristics (T<sub>A</sub>=25°C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS	
Static							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =250uA	40	-	-	V	
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =50uA	1.1	1.6	2.3		
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =20A	-	2	2.5	0	
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =20A	-	2.5	3.3	mΩ	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =40V, V <sub>GS</sub> =0V	-	-	1	uA	
Gate-Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	-	-	±100	nA	
Dynamic (Note 6)	•		•			•	
Total Gate Charge	$Q_g$	\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \	-	50	-		
Gate-Source Charge	Qgs	V <sub>DS</sub> =32V, I <sub>D</sub> =20A,	-	9	-	nC	
Gate-Drain Charge	$Q_{gd}$	V <sub>GS</sub> =10V	-	6	-		
Input Capacitance	Ciss	), osy, y, oy,	-	3125	-	pF	
Output Capacitance	Coss	V <sub>DS</sub> =25V, V <sub>GS</sub> =0V,	-	772	-		
Reverse Transfer Capacitance	Crss	f=1MHz	-	104	-		
Gate resistance	Rg	f=1MHz	-	1	-	Ω	
Turn-On Delay Time	td <sub>(on)</sub>	.,	-	16	-		
Turn-On Rise Time	tr	V <sub>DS</sub> =32V, I <sub>D</sub> =20A,	-	6	-		
Turn-Off Delay Time	td <sub>(off)</sub>	$V_{GS}=10V, R_{G}=3\Omega$ (Note 2)	-	49	-	ns	
Turn-Off Fall Time	tf	(Note 2)	-	11	-		
Drain-Source Diode	•			•	•		
Diode Forward Current	Is	T 05°0	-	-	151		
Pulsed Diode Forward Current	I <sub>SM</sub>	T <sub>C</sub> =25°C	-	-	604	A	
Diode Forward Voltage	V <sub>SD</sub>	Is=20A, V <sub>G</sub> s=0V	-	0.8	1.3	V	
Reverse Recovery Time	Trr	V <sub>GS</sub> =0V, I <sub>S</sub> =20A	-	40	-	ns	
Reverse Recovery Charge	Qrr	dls/dt=100A/us	-	34	-	nC	

#### NOTES:

- 1. Pulse width<100us, Duty cycle<2%.
- 2. Essentially independent of operating temperature typical characteristics.
- 3. Chip capability with an  $R_{\theta JC}$ =1.4°C/W, Package limited 100A.
- 4. R<sub>BJA</sub> is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch<sup>2</sup> with 2oz.square pad of copper.
- 5. The test condition is L=0.5mH, I<sub>AS</sub>=31A, V<sub>DD</sub>=30V, V<sub>GS</sub>=10V, Starting T<sub>J</sub>=25°C.
- 6. Guaranteed by design, not subject to production testing.





#### TYPICAL CHARACTERISTIC CURVES

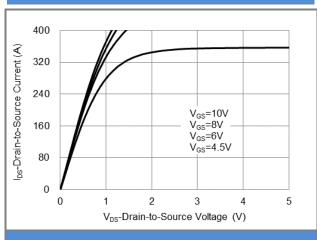
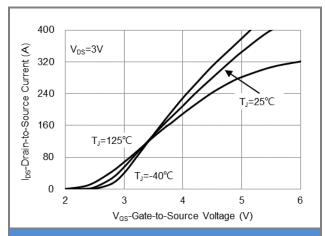


Fig.1 On-Region Characteristics



**Fig.2 Transfer Characteristics** 

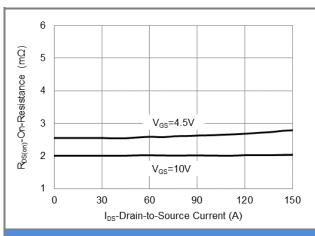


Fig.3 On-Resistance vs. Drain Current

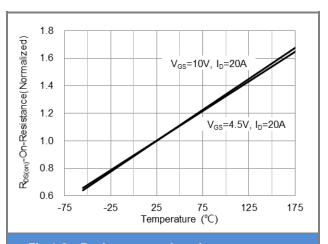
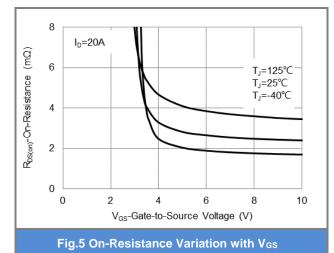
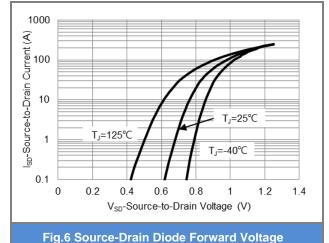


Fig.4 On-Resistance vs. Junction temperature









#### **TYPICAL CHARACTERISTIC CURVES**

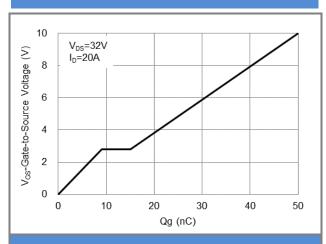


Fig.7 Gate-Charge Characteristics

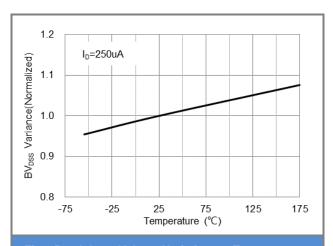


Fig.8 Breakdown Voltage Variation vs. Temperature

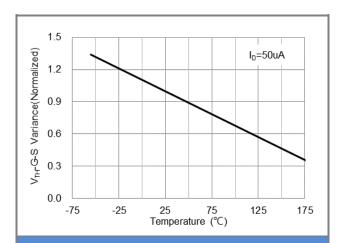


Fig.9 Threshold Voltage Variation with Temperature

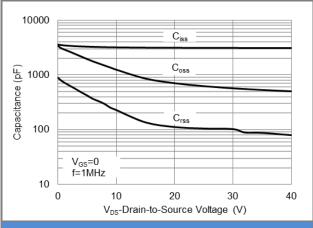
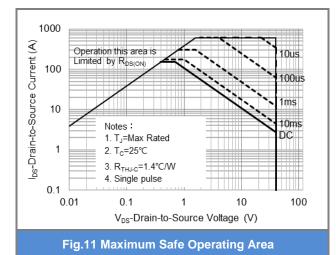


Fig.10 Capacitance vs. Drain-Source Voltage



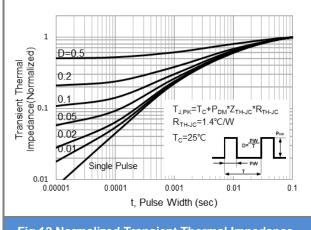


Fig.12 Normalized Transient Thermal Impedance

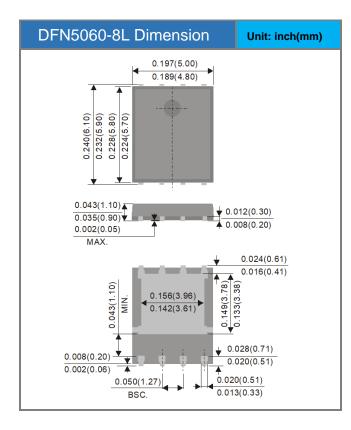


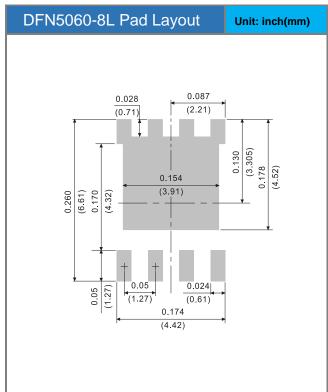


### **Product and Packing Information**

Part No.	Package Type	Packing Type	Marking	
PJQ5542-AU	DFN5060-8L	3K pcs / 13" reel	Q5542	

## **Packaging Information & Mounting Pad Layout**









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